

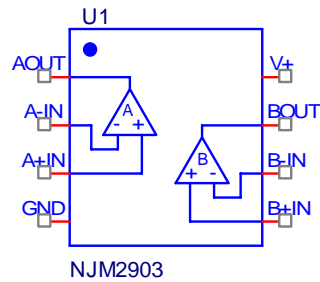
# Device Modeling Report

COMPONENTS:VOLTAGE COMPARATOR  
PART NUMBER:NJM2903  
MANUFACTURER:NEW JAPN RADIO



**Bee Technologies Inc.**

## Spice Model



```

*$
*PART NUMBER: NJM2903
*MANUFACTURER: New Japan Radio
*BJT COMPARATOR
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.subckt njm2903 AOUTPUT A-INPUT A+INPUT GND
+ B+INPUT B-INPUT BOUTPUT V+
X_U1 A+INPUT A-INPUT V+ GND AOUTPUT njm2903_s
X_U2 B+INPUT B-INPUT V+ GND BOUTPUT njm2903_s
.ends njm2903
*$
.subckt njm2903_s In+ li- V+ V- O/P
f1 9 V+ v1 1
iee V+ 7 dc 100.0E-6
vi1 21 In+ dc 0.74506
vi2 22 li- dc 0.752
q1 9 21 7 qin1
q2 8 22 7 qin2
q3 9 8 V- qmo
q4 8 8 V- qmi
.model qin1 PNP(Is=800.0E-18 Bf=.210200E3)
.model qin2 PNP(Is=800.0E-18 Bf=0.19500E3)
.model qmi NPN(Is=800.0E-18 Bf=1002)
.model qmo NPN(Is=800.0E-18 Bf=1000 Cjc=1E-15 Tr=57.8E-8)

```

```
e1  10  V-  9  V-  1
re1 101 V- 35
v1   10 11 dc 428m
q5   O/P 11 101 qoc
.model qoc NPN(Is=800.0E-18 Bf=7.3E3 Cjc=1E-15 Tf=0.365E-8 Tr=38.50E-8)
dp   V- V+ dx
rp   V+ V- 71.53
.model dx  D(Is=800.0E-18)
.ends njm2903_s
*$
```

## BJT MODEL

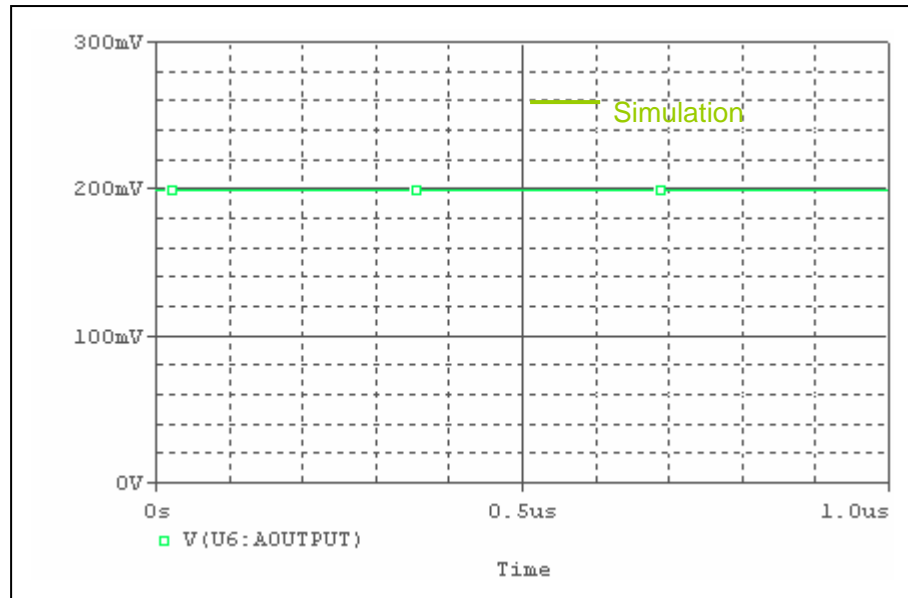
Pspice model parameter	Model description
IS	Saturation Current
BF	Ideal Maximum Forward Beta
CJC	Zero-bias Collector-Base Junction Capacitance
TF	Forward Transit Time
TR	Reverse Transit Time

## DIODE MODEL

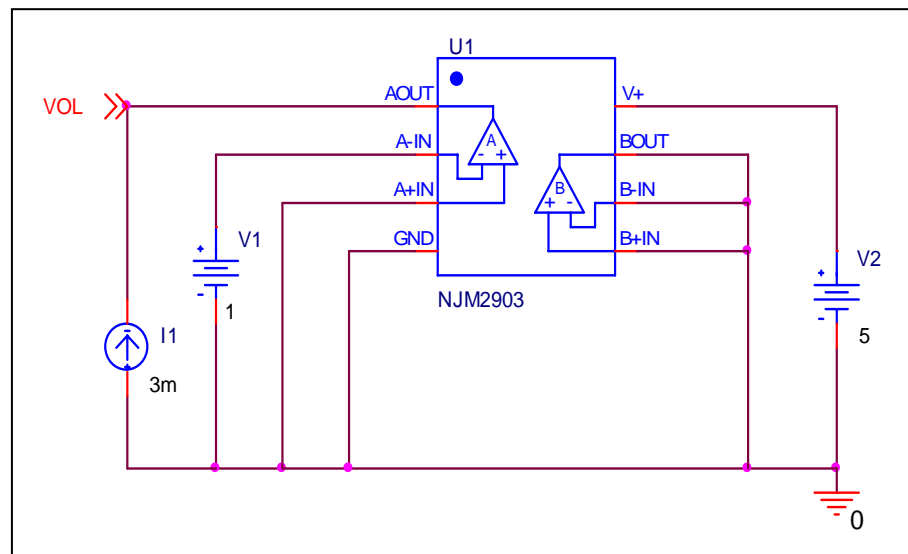
Pspice model parameter	Model description
IS	Saturation Current
RS	Series Resistance

## Output Low Voltage

### Simulation result



### Evaluation Circuit

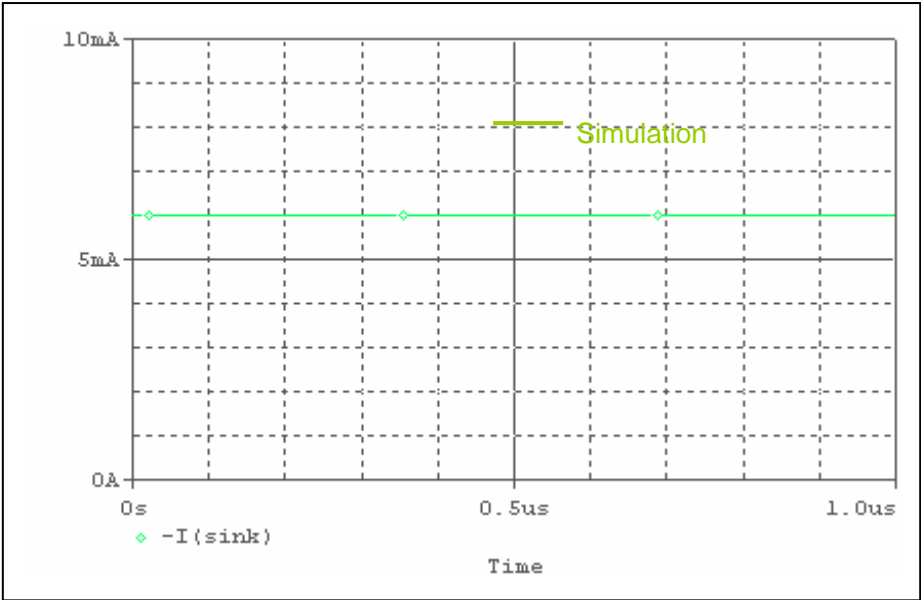


### Comparison Table

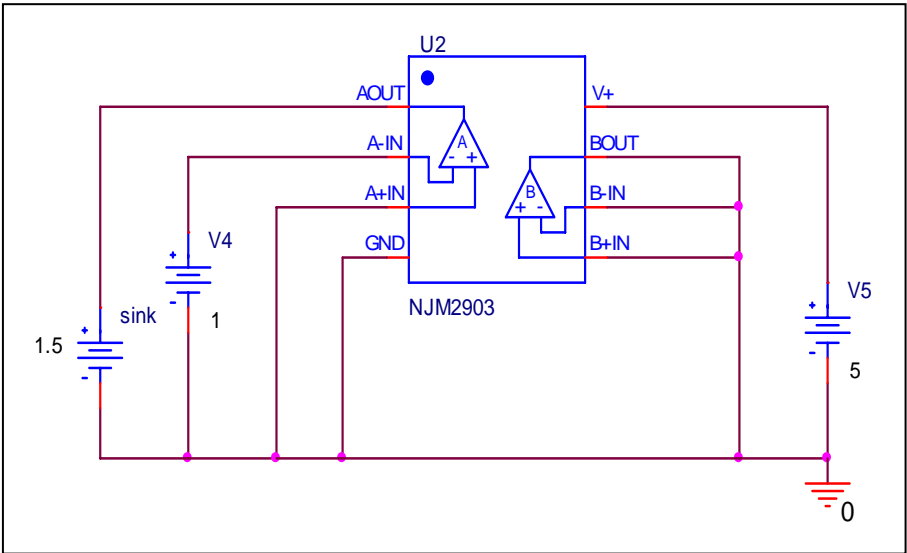
$I_{\text{sink}} = 3\text{mA}$	Measurement	Simulation	%Error
$V_{\text{ol}} \text{ (mV)}$	200	198.557	-0.7215

# Sink Current

## Simulation result



## Evaluation Circuit

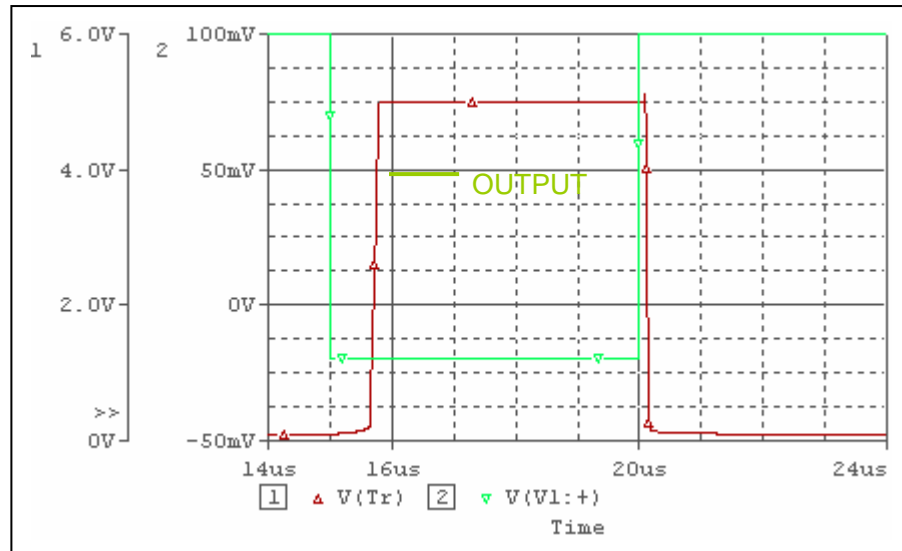


## Comparison Table

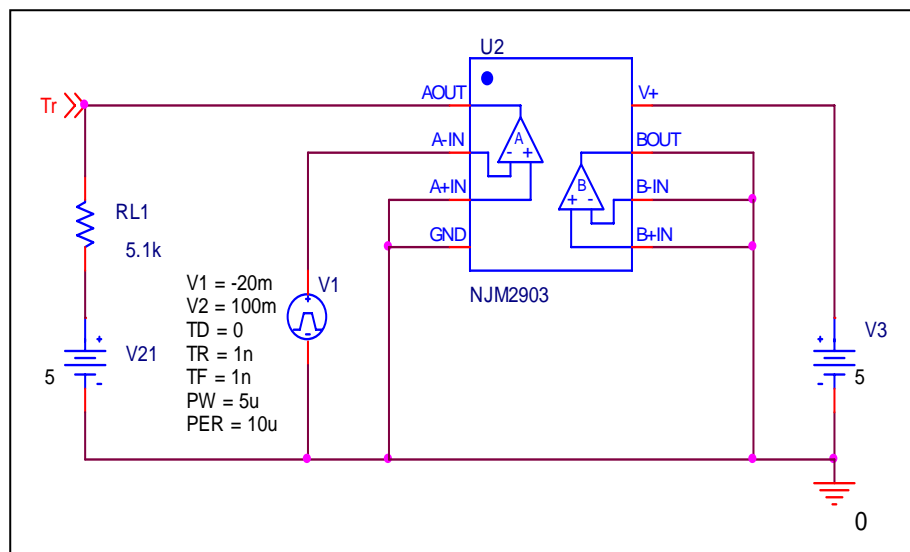
$V_{ol} = 1.5 \text{ V}$	Measurement	Simulation	%Error
$I_{\text{sink}} \text{ (mA)}$	6	6.0172	0.2867

## Response time (Rise time and Transition time)

### Simulation result



### Evaluation Circuit

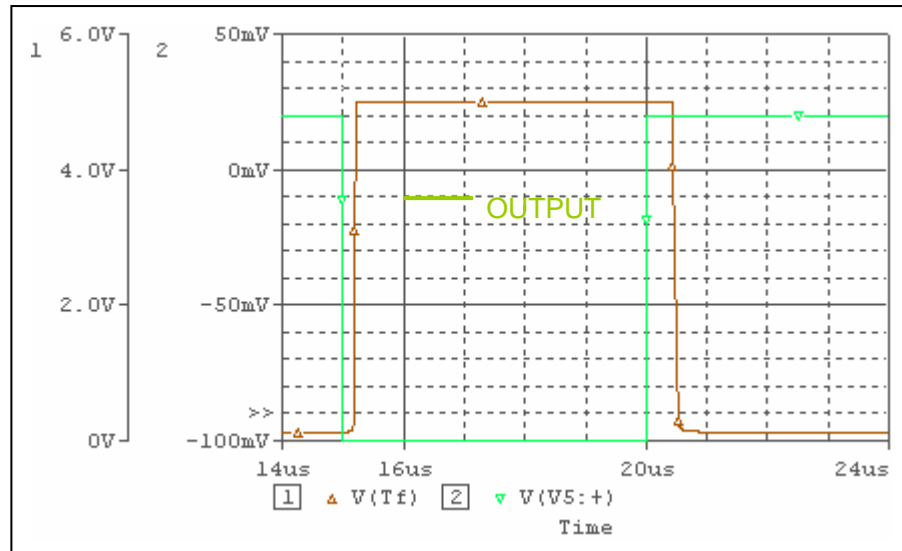


### Comparison Table

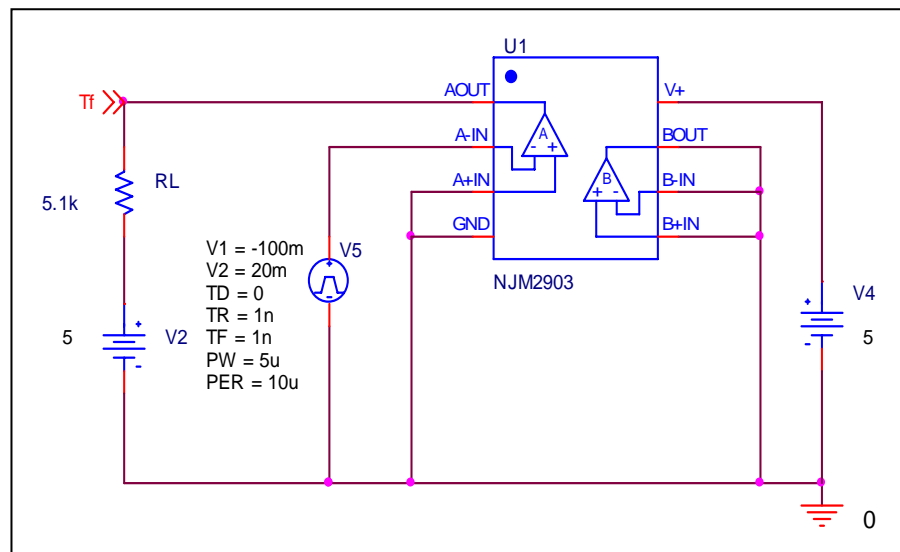
	Measurement	Simulation	% Error
Rising delay time (us)	0.63	0.628491	-0.2395
Transition time (us)	0.12	0.124967	4.1392

### Response time (Falling time)

### Simulation result



## Evaluation Circuit



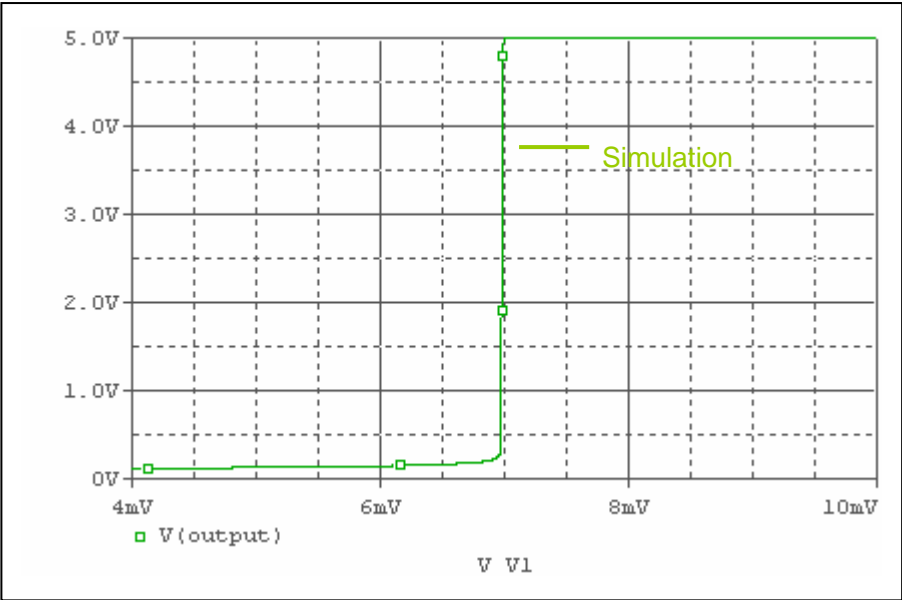
## Comparison Table

	Measurement	Simulation	% Error
Falling delay time (us)	0.43	0.429501	-0.1160

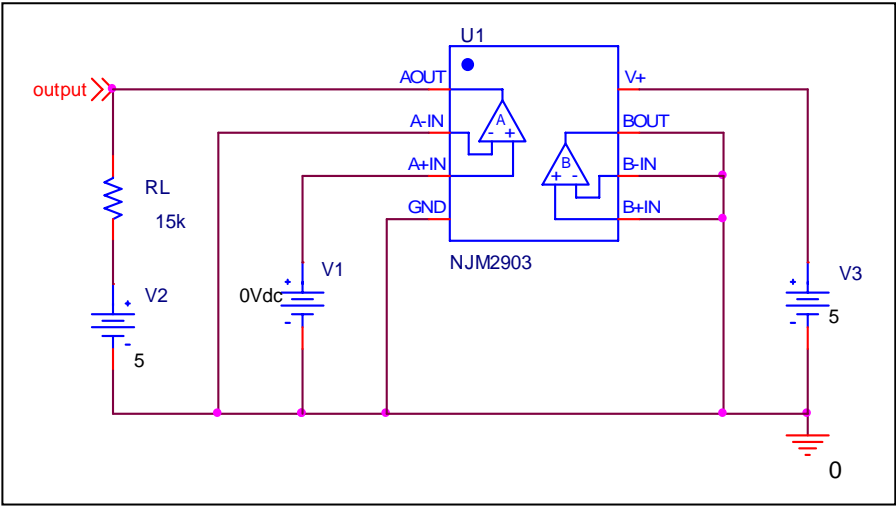


# Input Offset Voltage Characteristics

## Simulation result



## Evaluation Circuit

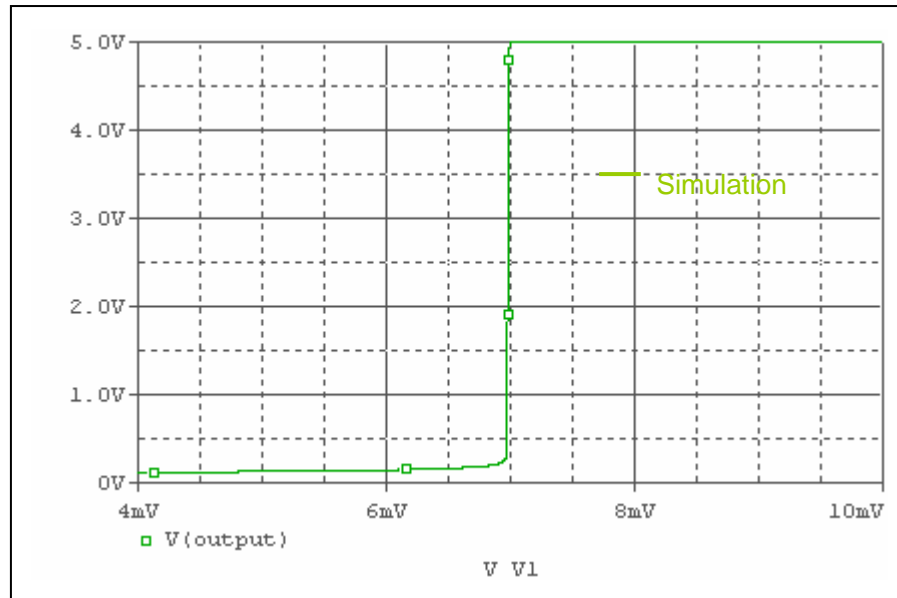


## Comparison Table

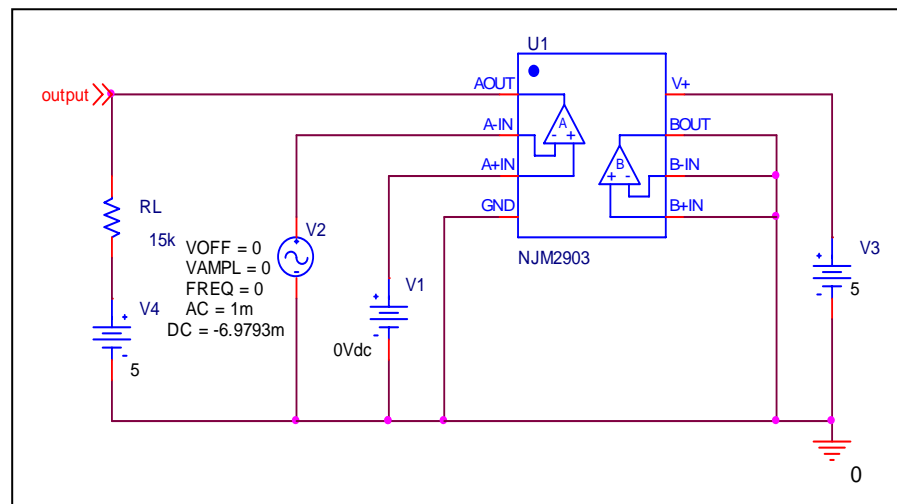
	Measurement	Simulation	%Error
$V_{io}(\text{mV})$	7	6.9793	-0.2957

## Av Characteristics

### Simulation result



### Evaluation Circuit

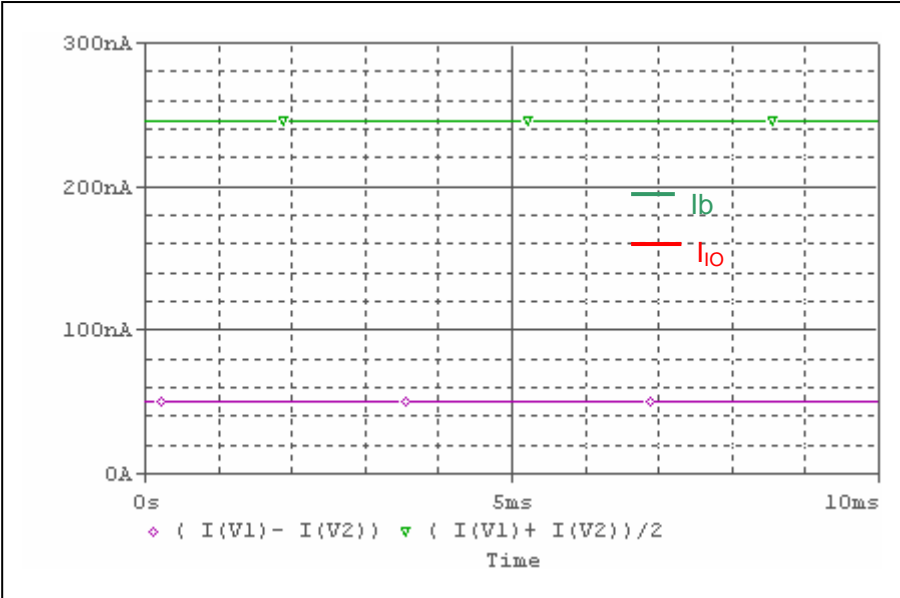


### Comparison Table

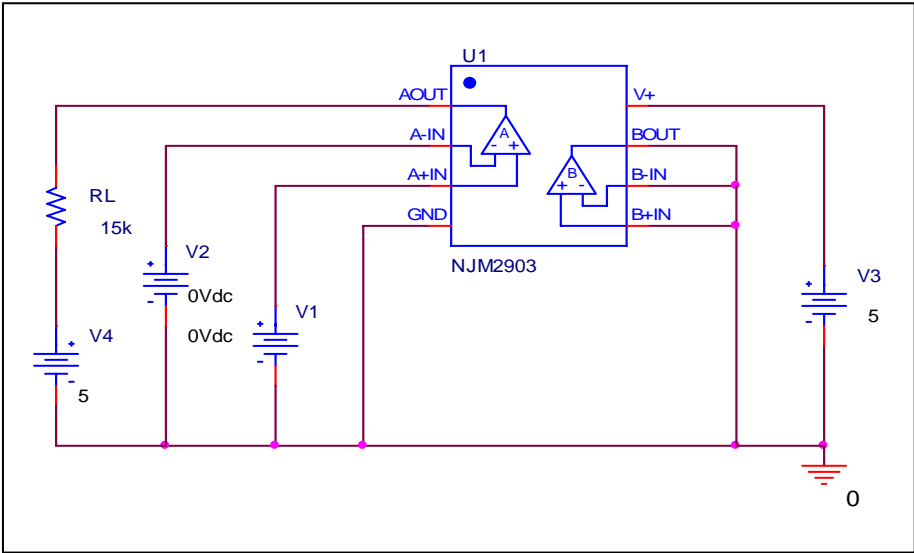
$R_L = 15k\Omega$	Measurement	Simulation	%Error
$A_v$ (dB)	106	105.599	-0.3783

# Input Bias Current Characteristics

## Simulation result



## Evaluation Circuit



## Comparison Table

	Measurement	Simulation	% Error
$I_b$ (nA)	50	49.804	-0.3920
$I_{io}$ (nA)	250	246.035	-1.5860